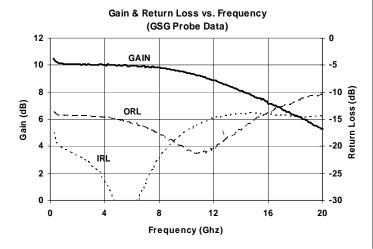




Product Description

Sirenza Microdevices' SUF-3000 is a monolithically matched broadband high IP3 gain block covering 0.25-16 GHz. This pHEMT FET-based amplifier uses a patented self-bias Darlington topology featuring a gain and temperature compensating active bias network that operates from a single 5V supply. It offers efficient, cascadable performance in a compact 0.88 x 0.80 mm² die. It is well-suited for RF, LO, and IF driver applications.



SUF-3000

0.25-16 GHz, Cascadable pHEMT MMIC Amplifier

Product Features

- Broadband Performance
- Gain = 10 dB @ 6 GHz
- P1dB = 15.5 dBm @ 6 GHz
- Low-noise, Efficient Gain Block
- 5V Operation, No Dropping Resistor
- Low Gain Variation vs. Temperature
- Patented Thermal Design
- Patented Self-Bias Darlington Circuit

Applications

- Broadband Communications
- Test Instrumentation
- Military & Space
- LO and IF Mixer Applications
- High IP3 RF Driver Applications

Symbol	Parameters	Units	Frequency	Min.	Тур.	Max.
G_{p}		dB	2 GHz		10.0	
	Small Signal Power Gain		6 GHz		10.0	
			14 GHz		8.0	
P1dB		dBm	2 GHz		16.0	
	Output Power at 1dB Compression		6 GHz		15.5	
			14 GHz		13.5	
OIP3	Output Third Order Intercept Point	dBm	2 GHz		27.0	
			6 GHz		26.5	
			14 GHz		19.5	
NF	Noise Figure	dB	2 GHz		4.2	
			6 GHz		4.8	
			14 GHz		5.0	
IRL	Input Return Loss	dB	2 GHz		-22.5	
			6 GHz		-32.5	
			14 GHz		14.0	
ORL	Output Return Loss	dB	2 GHz		-15.0	
			6 GHz		-16.5	
			14 GHz		-17.0	
Isol	Reverse Isolation	dB	2 GHz		-15.5	
			6 GHz		-15.0	
			14 GHz		-15.0	
V_D	Device Operating Voltage	V			5.0	
I _D	Device Operating Current	mA			51	
ΔG/ΔT	Device Gain Temperature Coefficient	dB/°C			-0.01	
Rth, j-l	Thermal Resistance (junction-to-backside)	°C/W			224	

Test Conditions: $V_D = 5.0V$, $I_D = 51mA$, OIP3 Tone Spacing = 1MHz, Pout per tone = 0 dBm $Z_S = Z_L = 50$ Ohms, 25C, GSG Probe Data With Bias Tees

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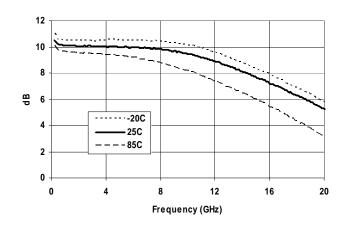
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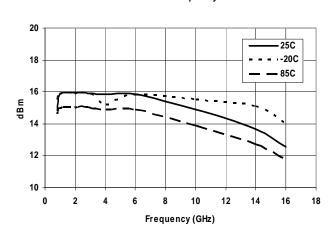


Typical Performance (GSG Probe Data)

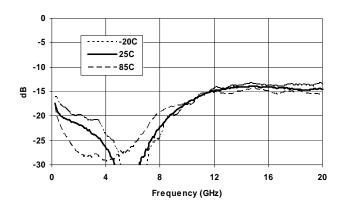
S21 vs. Frequency



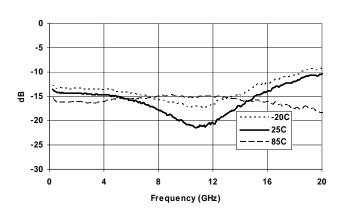
P1dB vs. Frequency



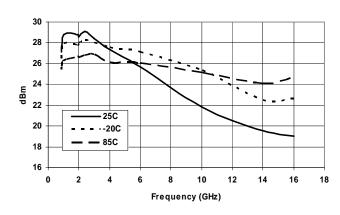
S11 vs. Frequency



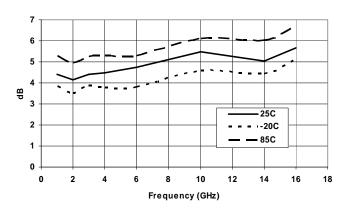
S22 vs. Frequency



OIP3 vs. Frequency



Noise Figure vs. Frequency





Typical Performance (GSG Probe Data)

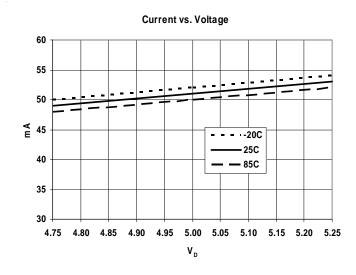
V _D	Current (mA)	Gain (dB)	P1dB	OIP3	S11	S22	NF (dB)
	`		(dBIII)	(dBIII)		·	(db)
5	51	10.0			-19.0	-14.0	
5	51	10.0	15.5	25.5	-21.0	-15.0	4.4
5	51	10.0	16.0	27.0	-22.0	-15.0	4.2
5	51	10.0	16.0	27.5	-27.0	-15.0	4.5
5	51	10.0	15.5	26.5	-32.0	-16.0	4.8
5	51	9.5	15.0	24.5	-17.0	-21.0	5.5
5	51	8.0	13.5	22.5	-14.0	-17.0	5.0
5	51	7.0	13.0	22.0	-14.5	-13.5	5.7
	5 5 5 5 5 5 5 5	(V) (mA) 5 51 5 51 5 51 5 51 5 51 5 51 5 51 5 51 5 51 5 51 5 51 5 51 5 51	(V) (mA) (dB) 5 51 10.5 5 51 10.0 5 51 10.0 5 51 10.0 5 51 10.0 5 51 10.0 5 51 9.5 5 51 8.0 5 51 7.0	(V) (mA) (dB) (dBm) 5 51 10.5 5 51 10.0 5 51 10.0 15.5 5 51 10.0 16.0 5 51 10.0 15.5 5 51 10.0 15.5 5 51 9.5 15.0 5 51 8.0 13.5 5 51 7.0 13.0	(V) (mA) (dB) (dBm) (dBm) 5 51 10.5 5 51 10.0 5 51 10.0 15.5 25.5 5 51 10.0 16.0 27.0 5 51 10.0 16.0 27.5 5 51 10.0 15.5 26.5 5 51 9.5 15.0 24.5 5 51 8.0 13.5 22.5 5 51 7.0 13.0 22.0	(V) (mA) (dB) (dBm) (dBm) (dB) 5 51 10.5 -17.5 5 51 10.0 -19.0 5 51 10.0 15.5 25.5 -21.0 5 51 10.0 16.0 27.0 -22.0 5 51 10.0 16.0 27.5 -27.0 5 51 10.0 15.5 26.5 -32.0 5 51 9.5 15.0 24.5 -17.0 5 51 8.0 13.5 22.5 -14.0 5 51 7.0 13.0 22.0 -14.5	(V) (mA) (dB) (dBm) (dBm) (dB) (dB) 5 51 10.5 -17.5 -13.5 5 51 10.0 -19.0 -14.0 5 51 10.0 15.5 25.5 -21.0 -15.0 5 51 10.0 16.0 27.0 -22.0 -15.0 5 51 10.0 16.0 27.5 -27.0 -15.0 5 51 10.0 15.5 26.5 -32.0 -16.0 5 51 9.5 15.0 24.5 -17.0 -21.0 5 51 8.0 13.5 22.5 -14.0 -17.0 5 51 7.0 13.0 22.0 -14.5 -13.5

Parameter	Absolute Limit		
Max Device Current (I _D)	60mA		
Max Device Voltage (V _D)	5.5V		
Max RF Input Power	10dBm		
Max Dissipated Power	330mW		
Max Junction Temperature (T _J)	150C		
Operating Temperature Range (T _L)	-40 to +85C		
Max Storage Temp.	-65 to +150C		

Operation of this device beyond any one of these limits may cause permanent damage. For reliable continuous operation, the device voltage and current must not exceed the maximum operating values specified in the table on page one.

Bias Conditions should also satisfy the following expression: $I_DV_D < (T_J - T_L) / R_{TH}$, j-l T_L =Backside of die

Current Variation vs. Temperature





ELECTROSTATIC SENSITIVE DEVICE Appropriate precautions in handling, packaging and testing devices must be observed.

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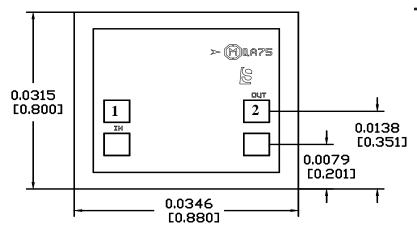
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Pad Description

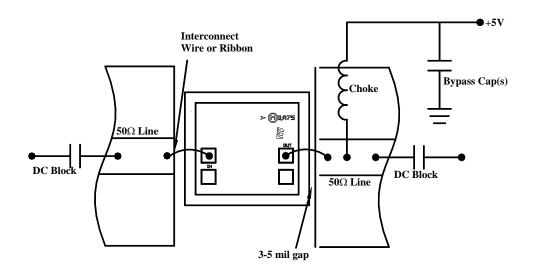


Pad #	Function	Description
1		This pad is DC coupled and matched to 50 Ohms. An external DC block is required.
2		This pad is DC coupled and matched to 50 Ohms. Bias is applied through this pad.
Die Bottom	GND	Die bottom must be connected to RF/DC ground using silver-filled conductive epoxy.

Notes:

- 1. All Dimensions in Inches [Millimeters].
- 2. No connection required for unlabeled bond pads.
- 3. Die Thickness is 0.004 (0.100).
- 4. Typical bond pad is 0.004 (0.100) square.
- 5. Backside metalization: Gold.
- 6. Backside is Ground.
- 7. Bond pad metalization: Gold.

Device Assembly



Phone: (800) SMI-MMIC